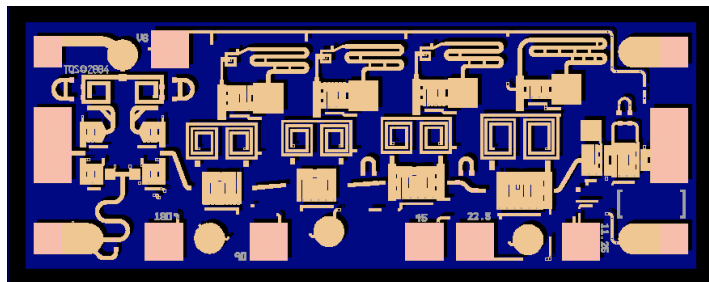


## 30 GHz 5-Bit Phase Shifter

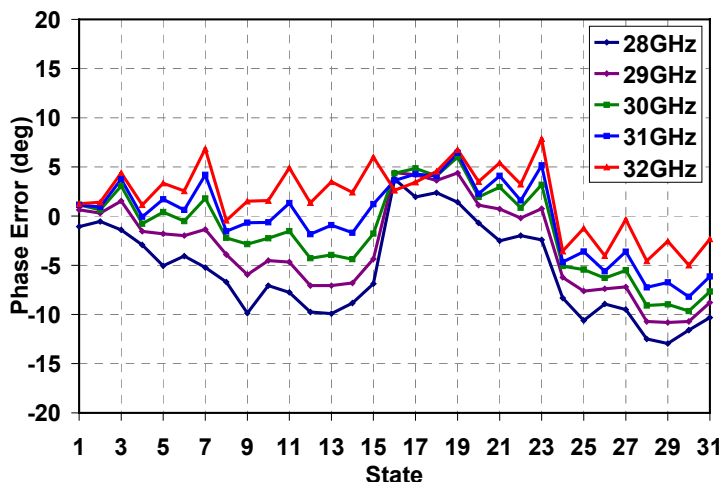
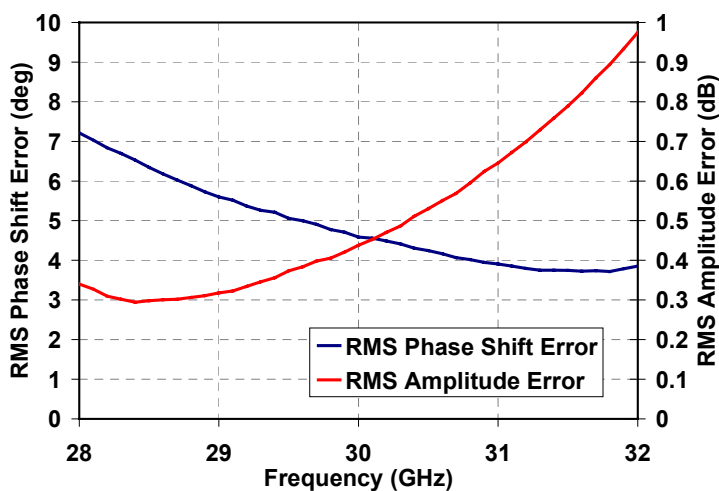
## TGP2100-EPU



### Key Features and Performance

- Positive Control Voltage
- Single-Ended Logic
- CMOS Compatible
- Frequency Range: 28 - 32 GHz
- 0.25µm pHEMT 3MI Technology
- Chip dimensions:  
1.88 x 0.75 x 0.1 mm  
(0.074 x 0.030 x 0.004 inches)

### Preliminary Measured Performance



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

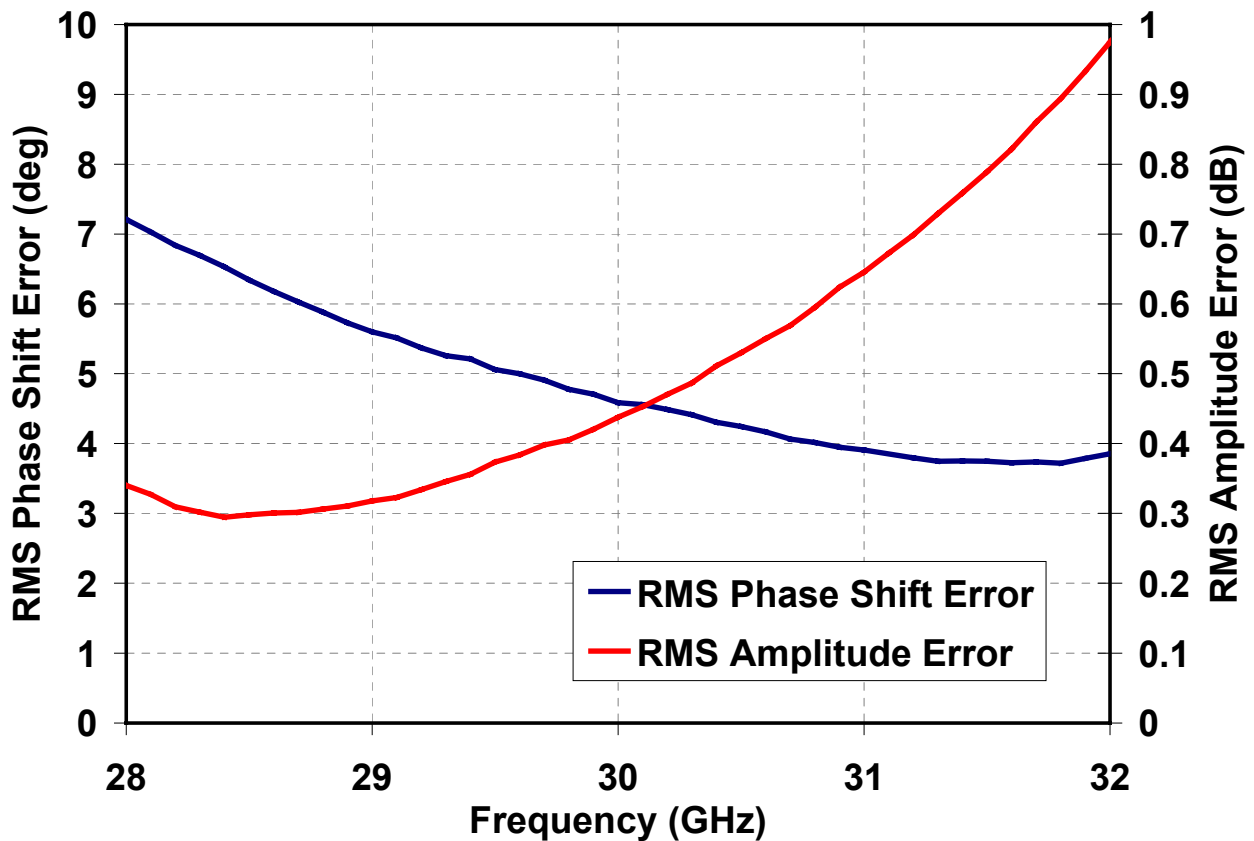
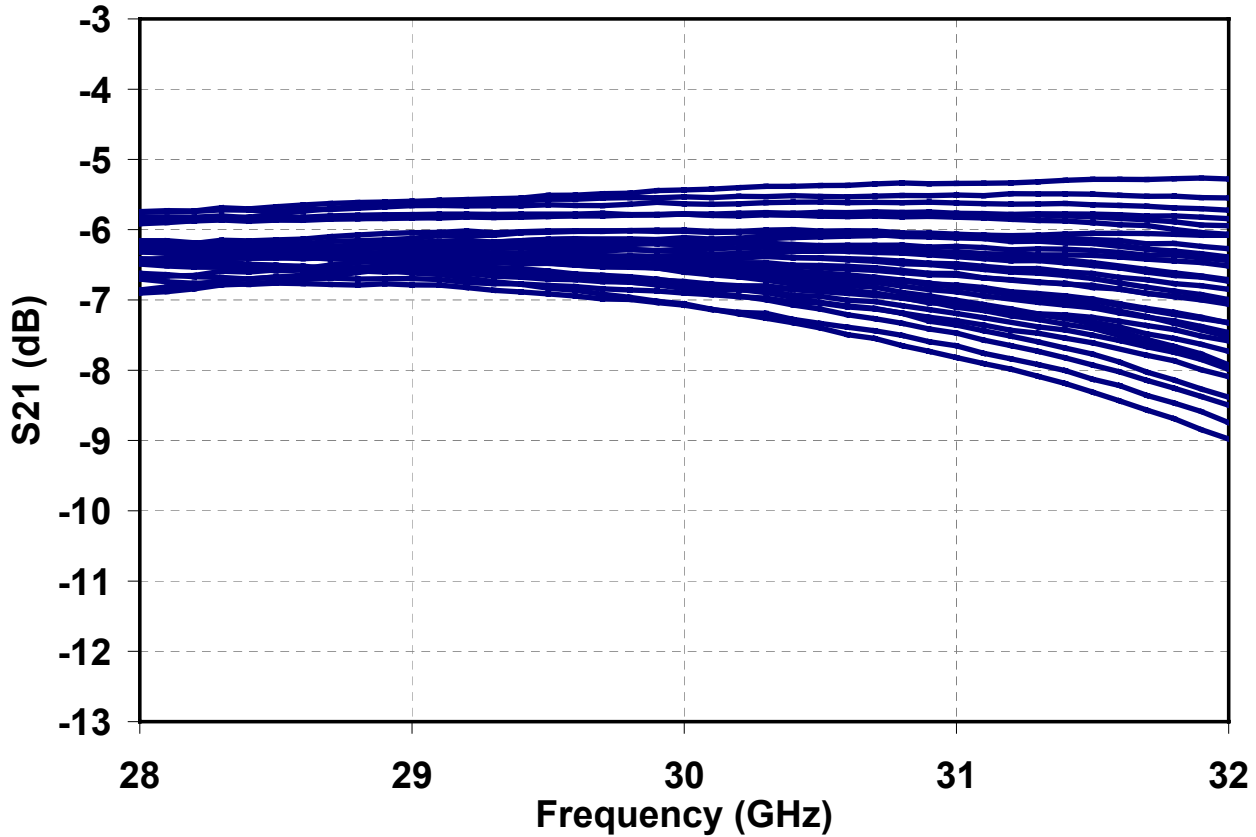
TABLE I  
MAXIMUM RATINGS

Symbol	Parameter	Value	Notes
V <sub>C</sub>	Control Voltage Range	0 - +8 V	<u>1/</u> <u>2/</u>
I <sub>D</sub>	Control Supply Current	1 mA	<u>1/</u> <u>2/</u>
P <sub>IN</sub>	Input Continuous Wave Power	20 dBm	<u>1/</u> <u>2/</u>
P <sub>D</sub>	Power Dissipation	0.1 W	<u>1/</u> <u>2/</u>
T <sub>CH</sub>	Operating Channel Temperature	150 °C	<u>3/</u>
T <sub>M</sub>	Mounting Temperature (30 Seconds)	320 °C	
T <sub>STG</sub>	Storage Temperature	-65 to 150 °C	

- 1/ These ratings represent the maximum operable values for this device
- 2/ Combinations of supply voltage, supply current, input power, and output power shall not exceed P<sub>D</sub> at a package base temperature of 70°C
- 3/ Junction operating temperature will directly affect the device median time to failure (MTTF). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.

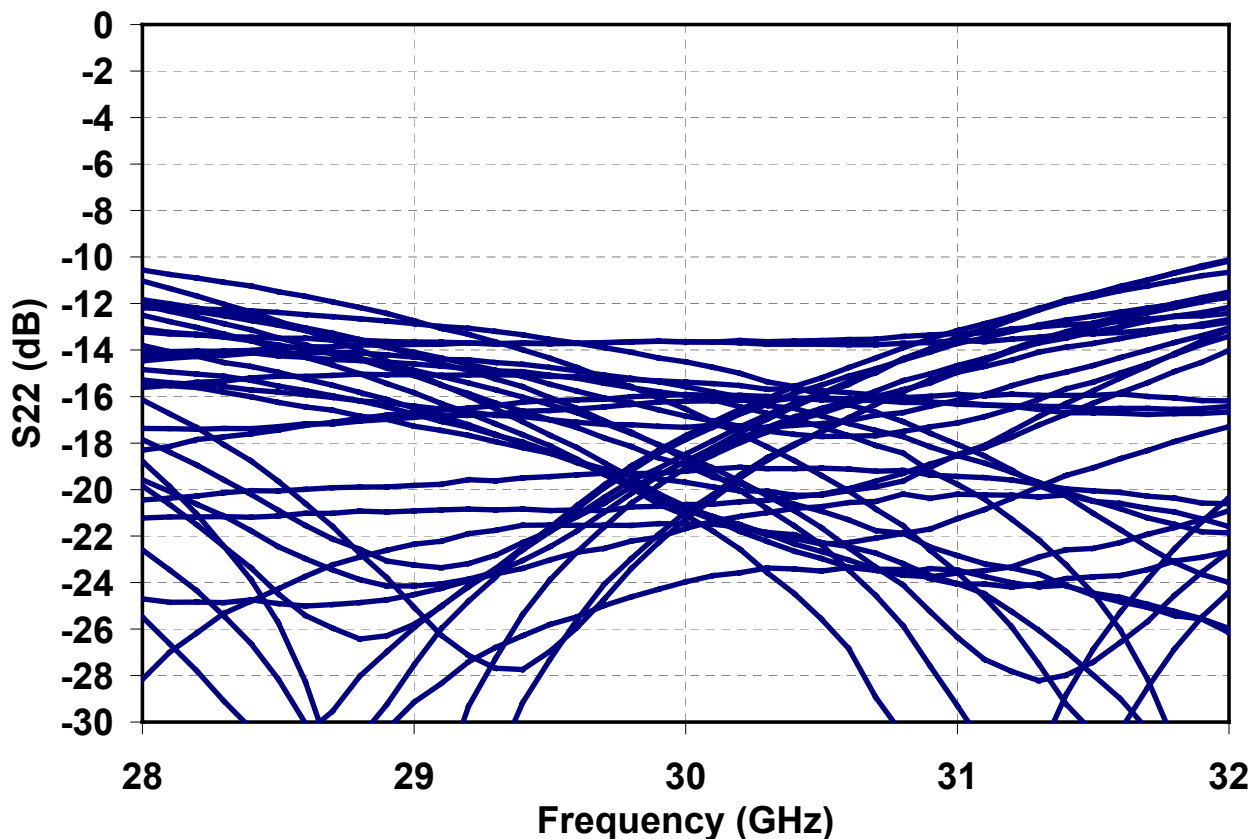
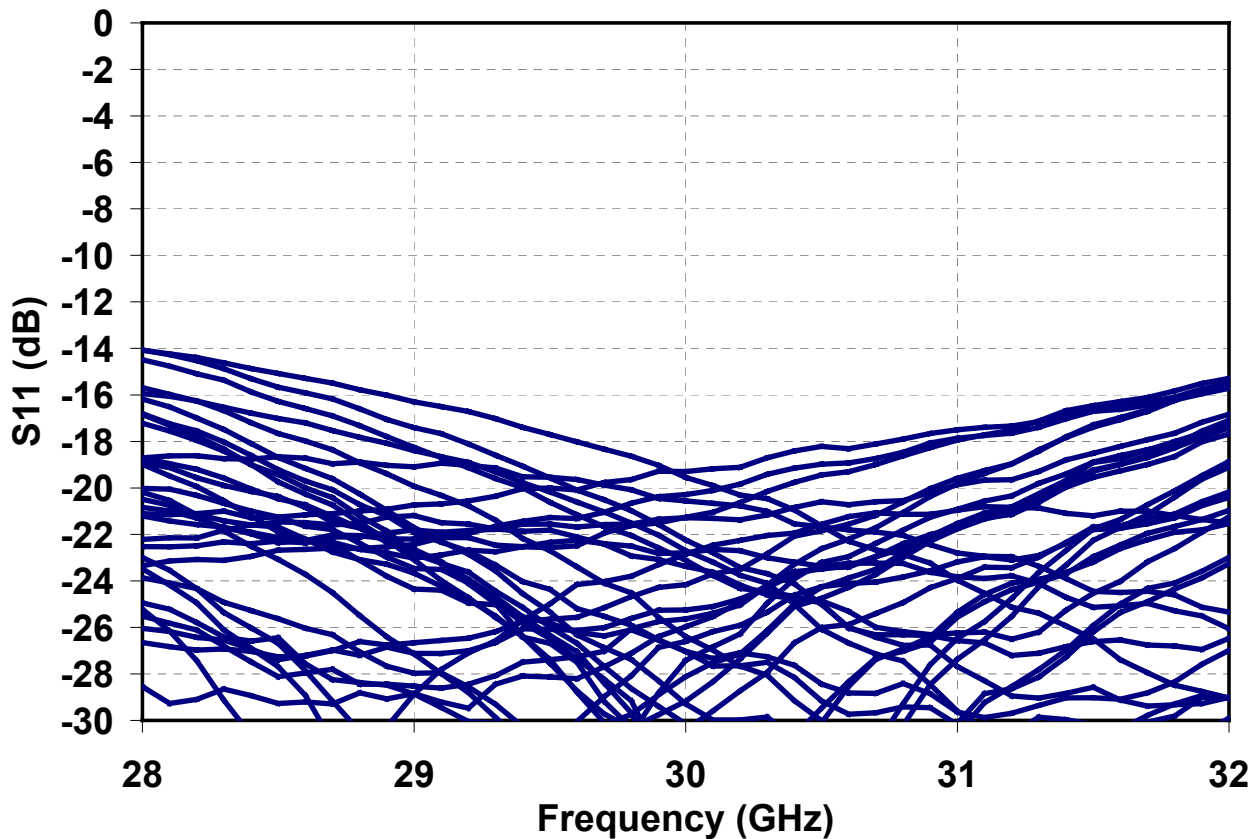
*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.*

Preliminary Measured Data



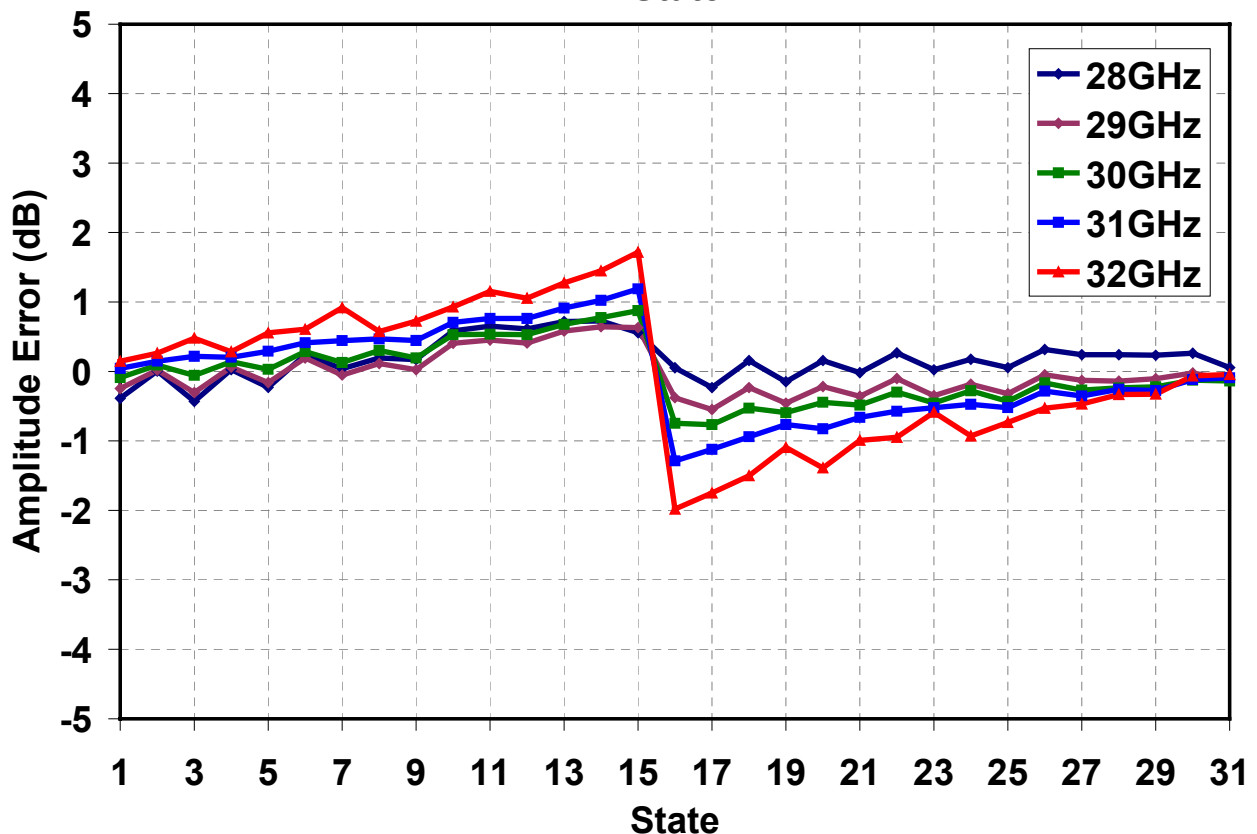
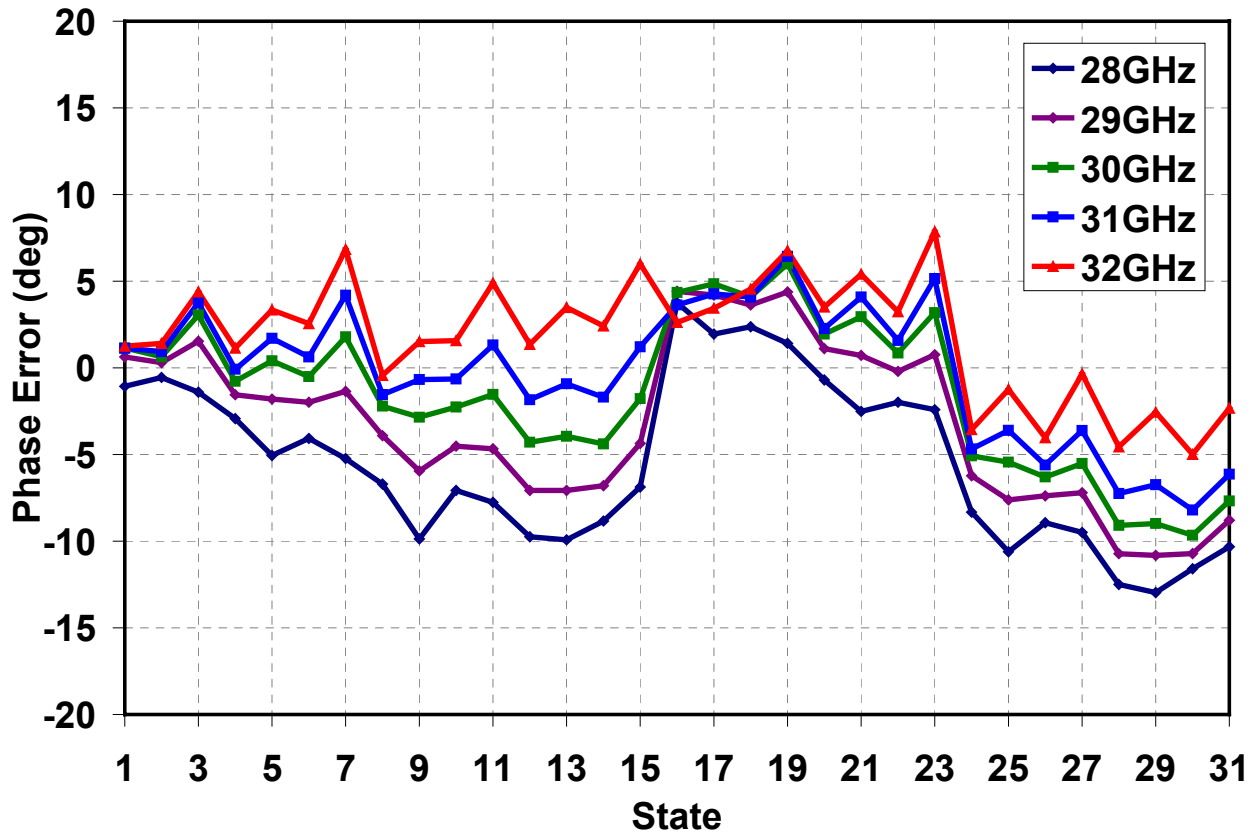
Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

Preliminary Measured Data



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

**Preliminary Measured Data**



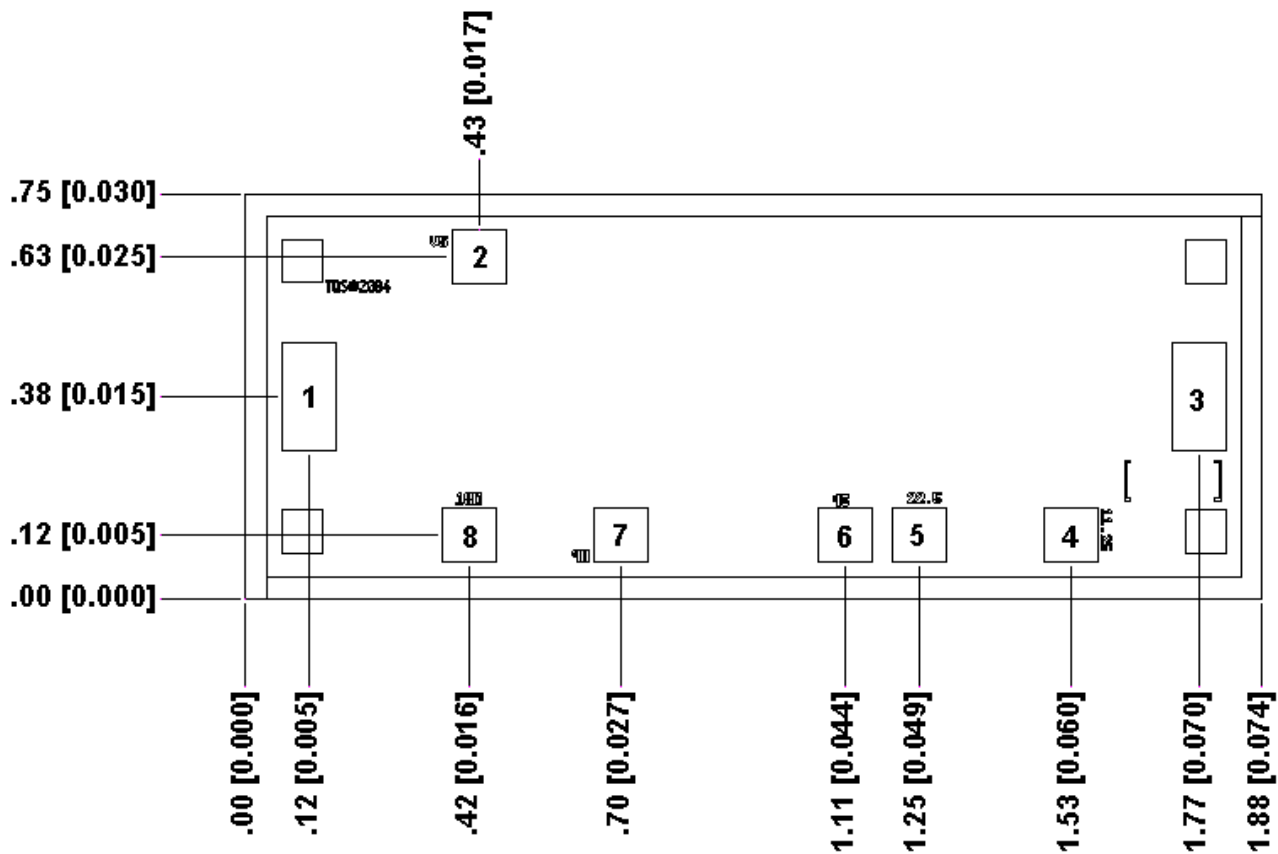
Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

**State Table**

State	V-Supply	V-11.25	V-22.5	V-45	V-90	V-180	Phase Shift
0	+5V	0V	0V	0V	0V	0V	Reference
1	+5V	+5V	0V	0V	0V	0V	11.25°
2	+5V	0V	+5V	0V	0V	0V	22.5°
3	+5V	+5V	+5V	0V	0V	0V	33.75°
4	+5V	0V	0V	+5V	0V	0V	45°
5	+5V	+5V	0V	+5V	0V	0V	56.25°
6	+5V	0V	+5V	+5V	0V	0V	67.5°
7	+5V	+5V	+5V	+5V	0V	0V	78.75°
8	+5V	0V	0V	0V	+5V	0V	90°
9	+5V	+5V	0V	0V	+5V	0V	101.25°
10	+5V	0V	+5V	0V	+5V	0V	112.5°
11	+5V	+5V	+5V	0V	+5V	0V	123.75°
12	+5V	0V	0V	+5V	+5V	0V	135°
13	+5V	+5V	0V	+5V	+5V	0V	146.25°
14	+5V	0V	+5V	+5V	+5V	0V	157.5°
15	+5V	+5V	+5V	+5V	+5V	0V	168.75°
16	+5V	0V	0V	0V	0V	+5V	180°
17	+5V	+5V	0V	0V	0V	+5V	191.25°
18	+5V	0V	+5V	0V	0V	+5V	202.5°
19	+5V	+5V	+5V	0V	0V	+5V	213.75°
20	+5V	0V	0V	+5V	0V	+5V	225°
21	+5V	+5V	0V	+5V	0V	+5V	236.25°
22	+5V	0V	+5V	+5V	0V	+5V	247.5°
23	+5V	+5V	+5V	+5V	0V	+5V	258.75°
24	+5V	0V	0V	0V	+5V	+5V	270°
25	+5V	+5V	0V	0V	+5V	+5V	281.25°
26	+5V	0V	+5V	0V	+5V	+5V	292.5°
27	+5V	+5V	+5V	0V	+5V	+5V	303.75°
28	+5V	0V	0V	+5V	+5V	+5V	315°
29	+5V	+5V	0V	+5V	+5V	+5V	326.25°
30	+5V	0V	+5V	+5V	+5V	+5V	337.5°
31	+5V	+5V	+5V	+5V	+5V	+5V	348.75°

*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.*

**Mechanical Drawing**



**Units: millimeters [inches]**

**Thickness: 0.10 [0.004] (reference only)**

**Chip edge to bond pad dimensions are shown to center of bond pads.**

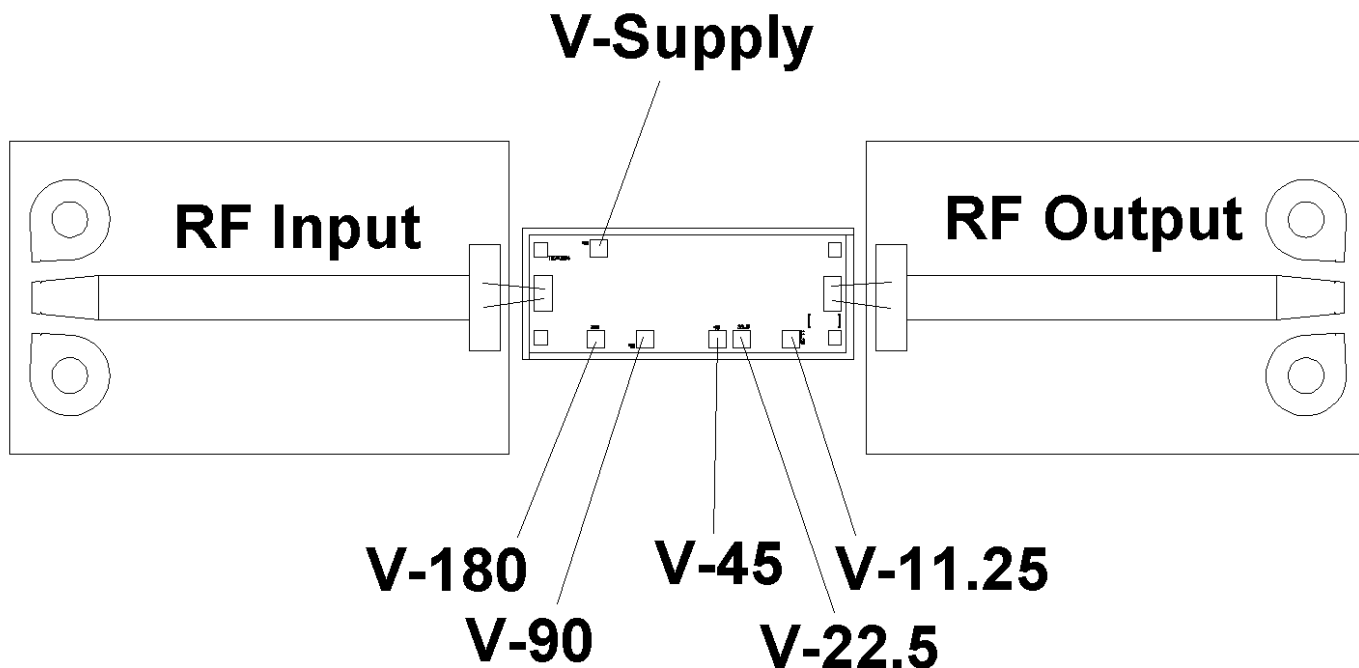
**Chip size tolerance: ±0.05 [0.002]**

**RF ground through backside**

<b>Bond Pad #1</b>	<b>RF Input</b>	<b>0.10 x 0.20</b>	<b>[0.004 x 0.008]</b>
<b>Bond Pad #2</b>	<b>V-Supply (+5V)</b>	<b>0.10 x 0.10</b>	<b>[0.004 x 0.004]</b>
<b>Bond Pad #3</b>	<b>RF Output</b>	<b>0.10 x 0.20</b>	<b>[0.004 x 0.008]</b>
<b>Bond Pad #4</b>	<b>V-11.25 (ON V=+5V)</b>	<b>0.10 x 0.10</b>	<b>[0.004 x 0.004]</b>
<b>Bond Pad #5</b>	<b>V-22.5 (ON V=+5V)</b>	<b>0.10 x 0.10</b>	<b>[0.004 x 0.004]</b>
<b>Bond Pad #6</b>	<b>V-45 (ON V=+5V)</b>	<b>0.10 x 0.10</b>	<b>[0.004 x 0.004]</b>
<b>Bond Pad #7</b>	<b>V-90 (ON V=+5V)</b>	<b>0.10 x 0.10</b>	<b>[0.004 x 0.004]</b>
<b>Bond Pad #8</b>	<b>V-180 (ON V=+5V)</b>	<b>0.10 x 0.10</b>	<b>[0.004 x 0.004]</b>

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### Chip Assembly & Bonding Diagram



**Devices were tested with 500Ω resistors in series with control lines**

*GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.*

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## Assembly Process Notes

Reflow process assembly notes:

- Use AuSn (80/20) solder with limited exposure to temperatures at or above 300°C. (30 seconds maximum)
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- No fluxes should be utilized.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.
- Microwave or radiant curing should not be used because of differential heating.
- Coefficient of thermal expansion matching is critical.

Interconnect process assembly notes:

- Thermosonic ball bonding is the preferred interconnect technique.
- Force, time, and ultrasonics are critical parameters.
- Aluminum wire should not be used.
- Maximum stage temperature is 200°C.

***GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.***

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